EEPROM Datasheet EEPROM V 1.1

Resources	PSoC® Blocks				API Memory (Bytes)	
	CapSense®	I2C/SPI	Timer	Comparator	Flash	RAM
CY8C20x66, CY8C20x36, CY8C20336AN, CY8C20436AN, CY8C20636AN, CY8C20xx6AS, CY8C20XX6L, CY8C20x46, CY8C20x96, CY8C20045, CY8C20055, CY7C645xx, CY7C643/4/5xx, CY7C60424, CY7C6053x, CYONS2000, CYONS2001, CYONS2100, CYONS2101, CYONS2110, CYONSFN2xxx, CYONSTB2xxx, CYONSFN2010-BFXC, CYONSCN2024-BFXC, CYONSCN2028-BFXC, CYONSCN2020-BFXC, CYONSKN2033-BFXC, CYONSKN2035-BFXC, CYONSKN2030-BFXC, CYONSTN2040, CY8CTMA140, CY8C20xx7/7S, CYRF89x35, CY8C20065, CY8C24x93, CY7C69xxx						
	–	–	–	–	900	0

Features and Overview

- Full byte-oriented EEPROM emulation
- Abstracts block-oriented flash architecture
- Efficient use of memory

The E2PROMx128 User Module emulates an EEPROM device within the flash memory of the PSoC device. The EEPROM device can be defined to start at any flash block boundary, with a byte length from 1 to the remainder of flash memory space. The API enables you to read and write 1 to N bytes at a time.

Figure 1.   E2PROMx128 Block Diagram
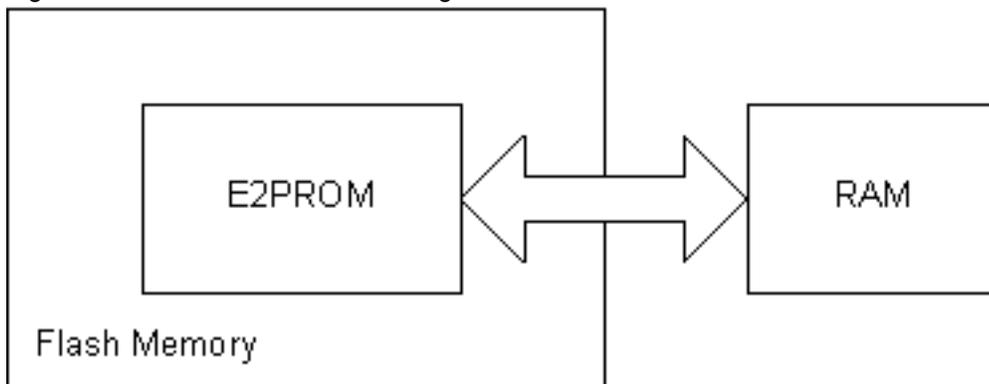
Functional Description

The E2PROMx128 User Module is a software algorithm that uses no hardware resources of the PSoC device. One or more instances of these EEPROM virtual devices can be created.

The flash is organized per device as 256 blocks of 128 bytes for a 32-K device. The architecture of the PSoC device allows the flash data to be read on a byte-by-byte basis, but requires the data to be written on a block-by-block basis – 128 bytes at a time. The intent of this user module is to emulate an EEPROM

device (a byte-read, byte-write oriented device) on a flash-based memory device (a byte-read, block-write oriented device).

The EEPROM storage area starts on a flash memory block boundary and consists of 1 or more bytes. This virtual device is accessed by using the E2PROMx128_E2Read() and E2PROMx128_bE2Write() API routines. The virtual address space is from 0 to N-1, where N is the length (size) in bytes of the EEPROM device. The size of the area reserved for storage must also be accounted for in flash memory usage but this quantity cannot be calculated by the resource meter. This size element is identified as 'Size' in the memory usage table.

The E2PROMx128_E2Read() API algorithm reads the flash memory byte-by-byte using the ROMX M8C instruction. This algorithm requires use of the last 8 bytes of RAM: 0xF8 to 0xFF.

The E2PROMx128_bE2Write() API algorithm writes data to the flash memory on a block-by-block basis. Based on the starting address offset into the EEPROM memory space, the E2PROMx128_bE2Write() routine parses the data to be written into segments that are aligned on block boundaries. This algorithm also requires use of the last 8 bytes of RAM: 0xF8 to 0xFF.

For segments that are less than the 128 bytes, a temporary 128-byte stack buffer is composed of both the unwritten and modified data. After the data is written, the buffer is released from the stack. This is required to preserve the unmodified data within the block. For segments that span an entire block, 128 bytes, no temporary buffer is created.

To reduce system overhead by optimizing parameters, see the Parameters and Resources section ahead.

Software Organization

The following figure shows how the software is organized into several layers consisting of two libraries and N EEPROM virtual device instances.

Resource usage (given in previous table) lists the API library size in flash plus the additional code contained in the FlashBlock API Library and the E2PROMx128 library. In cases where multiple instances of this device are used, only the user module E2PROMx128 API length is calculated in the resource meter. Only one FlashBlock API Library and E2PROMx128 Library is used for any number of user module instances.

Figure 2.   Library Structure

The flashblock API Library gives APIs that enable basic flash block read and write routines. These routines interface directly with the hardware and cause the device to enter System Supervisor mode. All interrupts are masked during this period. This library is only linked once, for all instances of the EEPROM virtual devices instantiated.

The E2PROMx128 Library translates block operations into byte-wise operations by way of block alignment and buffering. It then calls the flashblock API Library functions to write to the flash. This library is only linked once, regardless of the number of EEPROM virtual devices.

The EEPROM virtual device layer provides a simple means to allow multiple instances of an EEPROM device, while only incurring the overhead of a single instance of both the E2PROMx128 Library and the flashblock API Library. Each instance of the EEPROM virtual device contains a customized copy of this source code, which is minimal at only 16 bytes.

Both the E2PROMx128 and the flashblock API libraries are included in a library file. This file automatically links into the project if calls are made to these functions.

Note These libraries are not re-entrant.

Flash Write Cycle Longevity

The flash memory has a limit with respect to the total number of lifetime writes. The maximum number of flash read and write cycles is 50,000; for more details, see the specific device family's datasheet.

Flash Protection

The *flashsecurity.txt* file must be edited to allow flash writes to the blocks that comprise the EEPROM device.

Timing

Unless otherwise specified in the following table, all limits guaranteed for T_A = 25°C, V_{DD} = 5.0V.

Table 1. The timing of the EEPROM algorithms is summarized in the following table:

Parameter	Typical	Limit	Units	Conditions and Notes
Time to Write 0°C-100°C	45	120[3,4]	ms/Block	Time to write depends on the number of flash blocks that require an update.[1,2]
Time to Write -40°C-0°C	70	240[3,4]	ms/Block	Time to write depends on the number of flash blocks that require an update.[1,2]
Time to Read	81 + 46N	--	CPU clock cycles	N is the number of bytes read.

Timing Table Notes

1. Interrupts are masked during flash read and write operations during the time the M8C is in System Supervisor mode.
2. Time to Write is determined by the FlashBlockWrite() routine to erase and write each flash block.
3. Total number of flash writes is limited. See the part-specific datasheet for specifications on number of write cycles per block.
4. Limit is specified for normal programmed operation. In emulation mode using the debugger, the write pulse may take up to 1 to 2 seconds.

DC and AC Electrical Characteristics

See the device datasheet for your PSoC device for the electrical characteristics of the EEPROM.

Placement

The EEPROMx128 User Module is implemented in software and does not require placement.

Parameters and Resources

FirstBlock

The FirstBlock is the starting block in which the EEPROM device resides. Values range from 0 to the maximum number of flash blocks for the specific device: 255 for 32K devices, 127 for 16K devices, 63 for 8K devices, 31 for 4K devices, and 15 for 2K devices.

Special care must be taken to ensure that the E2PROM User Module's flash memory location does not overlap any code or other important data located in the flash. You should locate the E2PROM memory location as high as possible in the flash memory. For instance, if the device has 512 blocks of flash, locating the E2PROM User Module at flash block 511 would be a good choice. Locating it at flash block 0 or 1 would likely cause a system failure, since the E2PROM location overlaps the interrupt vectors. Any write operation to an E2PROM at block 0 or 1 would overwrite the interrupt vector table. Locating the E2PROM near the middle of the flash memory is also not a good practice. The ImageCraft compiler does not reserve a separate memory area for the E2PROM. Therefore, as your code gets larger, it eventually overlaps the E2PROM location near the middle of the flash memory.

Length

The length defines the size, in bytes, of the EEPROM device. The valid range is from 1 to N, where N is the size of EEPROM virtual device in bytes.

WARNING Ensure that the physical location of the virtual EEPROM device does not exceed the flash size of the device. The first physical byte of the EEPROM device is located at FirstBlock * 128. The last byte of the virtual device is physically located at (FirstBlock + Length - 1) * 128. Error checking is not performed. Failure to ensure that the size is not exceeded may result in unpredictable flash writes to unintended blocks.

RAM Memory Overhead

The following RAM memory resources are used:

API Routine	Memory Utilization
E2PROMx128_E2Read()	Stack Space: 8 Bytes RAM High Memory: 0xF8 – 0xFF
E2PROMx128_bE2Write() with NO Partial Block Writes	Stack Space: 32 Bytes RAM High Memory: 9 Bytes 0xF8 – 0xFF
E2PROMx128_bE2Write() with Partial Block Writes	Stack Space: 103 Bytes RAM High Memory: 9 Bytes 0xF8 – 0xFF

Efficient Memory Use

Use the following guidelines to maximize the efficiency of both RAM and flash resources:

- If flash memory is plenty (faster, more efficient use of RAM)

    - Create EEPROM devices in multiples of 128-byte lengths, even if the data to be stored is less.

    - Always write the data in multiples of 128-byte lengths.

    - Always read the data with the correct byte count.

For example, Serial Number Data is 10 bytes in length. Create an E2PROMx128 User Module with the name serial number. Set the Length parameter to 128. This allocates a 128-byte block in flash memory. In RAM, set up a 10-byte data array to hold the serial number data. When writing the serial number using E2Write(), specify the wByteCount parameter as 128. However, when reading the serial number data, specify the wByteCount parameter as 10.

■ If flash memory is at a premium (efficient use of flash)

- Create EEPROM devices using only the required number of bytes.

- Always write the data with the correct byte count.

- Always read the data with the correct byte count.

Application Programming Interface

The Application Programming Interface (API) routines are provided as part of the user module to allow the designer to deal with the module at a higher level. This section specifies the interface to each function together with related constants provided by the "include" files.

Each time a user module is placed, it is assigned an instance name. By default, PSoC Designer assigns the E2PROMx128_1 to the first instance of this user module in a given project. It can be changed to any unique value that follows the syntactic rules for identifiers. The assigned instance name becomes the prefix of every global function name, variable and constant symbol. In the following descriptions the instance name has been shortened to E2PROMx128 for simplicity.

Note

** In this, as in all user module APIs, the values of the A and X registers may be altered by calling an API function. The same is true for all RAM page pointer registers in the Large Memory Model. It is the responsibility of the calling function to preserve the values of A and X before the call if those values are required after the call. This "registers are volatile" policy was selected for efficiency reasons and has been in force since version 1.0 of PSoC Designer. The C compiler automatically takes care of this requirement. Assembly language programmers must ensure their code observes the policy, too. Though some user module API functions may leave A and X unchanged, there is no guarantee they may do so in the future.

For Large Memory Model devices, it is also the caller's responsibility to preserve any value in the CUR_PP, IDX_PP, MVR_PP, and MVW_PP registers. Even though some of these registers may not be modified now, there is no guarantee that will remain the case in future releases.

The EEPROMx128 User Module APIs are described in this section.

E2PROMx128_Start

Description:

A null function, maintained for user module API consistency.

C Prototype:

```
void  E2PROMx128_Start(void)
```

Assembler:

```
lcall  E2PROMx128_Start
```

Parameters:

None

Return Value:

None

Side Effects:

The A and X registers may be modified by this or future implementations of this function. The same is true for all RAM page pointer registers in the Large Memory Model in the CY8C29xxx. When necessary, it is the calling function's responsibility to preserve the values across calls to fastcall16 functions.

E2PROMx128_Stop

Description:

A null function, maintained for user module API consistency.

C Prototype:

```
void  E2PROMx128_Stop(void)
```

Assembler:

```
lcall  E2PROMx128_Stop
```

Parameters:

None

Return Value:

None

Side Effects:

The A and X registers may be modified by this or future implementations of this function. The same is true for all RAM page pointer registers in the Large Memory Model in the CY8C29xxx. When necessary, it is the calling function's responsibility to preserve the values across calls to fastcall16 functions.

E2PROMx128_bE2Write

Description:

Writes the specified data to the defined EEPROM from a RAM buffer. Note that the "flashsecurity.txt" file must be set properly to allow writing to flash. The cTemperature parameter is for backward compatibility. It does not do anything, so it can be assigned to 0 when calling this function. The device families that are supported by this user module have an internal capability to calculate die temperature before writing to flash. Die temperature is calculated automatically before each flash-write operation. As a result, you do not have to supply temperature when calling this API.

C Prototype:

```
CHAR  E2PROMx128_bE2Write(WORD wAddr, BYTE *pbData, WORD wByteCount,
                 CHAR cTemperature);
```

Assembly:

```
push  X
mov   X, SP
mov   A, <cTemperature>                ; cTemperature argument
push  A
mov   A, <wByteCount>                   ; wByteCount - MSB
push  A
mov   A, <wByteCount+1>                 ; wByteCount - LSB
```

```
push  A
mov   A, <pbData>                       ; pbData - MSB
push  A
mov   A, <pbData+1>                     ; pbData - LSB
push  A
mov   A, <wAddr>                        ; wAddr - MSB
push  A
mov   A, <wAddr+1>                      ; wAddr - LSB
push  A
lcall  E2PROMx128_bE2Write
add   SP, -E2_WR_ARG_STACK_FRAME_SIZE ; restore call stack
pop   X
```

Where <..> refers to any addressing mode or number of instructions to place referenced data into the Accumulator.

Parameters:

wAddr: Address offset of the EEPROM device address space from which the RAM data is written. It can be 0 to the N-1, where N is the length of the EEPROM device.

pbData: Pointer to the RAM buffer that contains data to write.

wByteCounter: Number of bytes to write to flash.

cTemperature: Temperature of the PSoC die, in degrees Celsius. This value can be specified by using one of the following:

- An user module, such as the FlashTemp User Module.
- An external device or sensor.
- A nominal value that applies to all environmental conditions that the PSoC device experiences.

    For example, room temperature = 25°C.

Return Values:

The following values can be returned:

Return Flag	Description	Value
E2PROMx128_NOERROR	Successful completion of operation.	0
E2PROMx128_FAILURE	Unsuccessful completion of operation. Most likely a result of flash-protection bit errors.	-1
E2PROMx128_STACKOVERFLOW	Stack space was not sufficient for algorithm requirements.	-2

Side Effects:

The A and X registers may be modified by this or future implementations of this function. The same is true for all RAM page pointer registers in the Large Memory Model in the CY8C29xxx. When necessary, it is the calling function's responsibility to preserve the values across calls to fastcall16 functions. Currently, only the CUR_PP, IDX_PP and MVW_PP page pointer registers are modified.

E2PROMx128_E2Read

Description:

Reads the specified EEPROM device data from flash into the specified RAM buffer.

C Prototype:

```
void E2PROMx128_E2Read(WORD wAddr, BYTE *pbData, WORD wByteCount)
```

Assembler:

```
push  X
mov   X, SP
mov   A, <wByteCount>              ; wByteCount - MSB
push  A
mov   A, <wByteCount+1>            ; wByteCount - LSB
push  A
mov   A, <pbDataDest>             ; pbDataDest - MSB
push  A
mov   A, <pbDataDest+1>           ; pbDataDest - LSB
push  A
mov   A, <wAddr>                  ; wAddr - MSB
push  A
mov   A, <wAddr+1>                ; wAddr - LSB
push  A
lcall   E2PROMx128_E2Read
add   SP, -E2_RD_ARG_STACK_FRAME_SIZE  ; restore call stack
pop   X
```

Where <..> refers to any addressing mode or number of instructions to place referenced data into the Accumulator.

Parameters:

wAddr: Address offset of the EEPROM device address space from which the flash data is read. It can be 0 to the N-1, where N is the length of the EEPROM device.

pbData: Pointer to the RAM buffer that data is read into.

wByteCounter: Number of bytes to read from flash.

Return Value:

None

Side Effects:

The A and X registers may be modified by this or future implementations of this function. The same is true for all RAM page pointer registers in the Large Memory Model in the CY8C29xxx. When necessary, it is the calling function's responsibility to preserve the values across calls to fastcall16 functions. Currently, only the CUR_PP and MVW_PP page pointer registers are modified.

Sample Firmware Source Code

The following is C language source code. This sample code was developed for a CY7C64215 device family. Other device families supported by this user module may have differences in available ports, pins, and available drive modes. Some customization of this code may be necessary to make it operate on your device.

```c
//**********************************************************************
//*     EEPROM User Module Example Code:
//*
//*     A SerialNumber EEPROM was created to start at block 250 with a length
//*     of 10 bytes. Remember to edit the Flashsecurity.txt file to allow
//*     writes to flash  (Set the 250th block to U - Unprotected).
//*
//*     This example:
//*
//*         a) Writes the initial data to the EEPROM block area
//* Note that this will invoke the SavePartial algorithm which
//* allocates a temporary 64-byte buffer on the stack. If
//* Flash memory is plentiful and the extra 54 bytes can be
//* wasted, set the SerialNumber device to a length of 64 and when
//* writing, specify a bytecount of 64. This will write an entire
//* block without using a temporary buffer. The extra 54 bytes
//* beyond the SerialNumber will be bogus data.
//*
//*         b) Reads the data back into a RAM buffer
//*
//**********************************************************************/

#include <m8c.h>          // part specific constants and macros
#include "PSoCAPI.h"      // PSoC API definitions for all User Modules

#define   ADDRESS_OFFSET    0
#define   NUMBER_OF_BYTES   10
#define   TEMPERATURE       25

/* Initialize a RAM buffer with default Serial Number */
BYTE  abInitialSerialNumber[] = {'0','1','2','3','4','5','6','7','8','9' };
BYTE  abSerialNumberBuffer[NUMBER_OF_BYTES];

void main(void)
{
    BYTE bError;


/* Write the Serial Number - assume temp of 25C */
    bError = E2PROMx128_bE2Write(ADDRESS_OFFSET, abInitialSerialNumber,
NUMBER_OF_BYTES, TEMPERATURE);


if ( bError == E2PROMx128_NOERROR )
    {
        /* Read the Serial Number back into a RAM buffer */
        E2PROMx128_E2Read( ADDRESS_OFFSET, abSerialNumberBuffer, NUMBER_OF_BYTES );
    }
```

```
    while(1)
    {
    }
}
```

The same code in assembly is:

```
;************************************************************************
;     EEPROM User Module Example Code:
;
;     A SerialNumber EEPROM was created to start at block 250 with a length
;     of 10 bytes. Remember to edit the Flashsecurity.txt file to allow
;     writes to flash (Set the 250th block to U - Unprotected).
;
;     This example:
;
;         a) Writes the initial data to the EEPROM block area
;          Note that this will invoke the SavePartial algorithm which
;         allocates a temporary 64-byte buffer on the stack. If
;          flash memory is plentiful and the extra 54 bytes can be
;          wasted, set the SerialNumber device to a length of 64 and when
;          writing, specify a bytecount of 64. This will write an entire
;          block without using a temporary buffer. The extra 54 bytes
;          beyond the SerialNumber will be bogus data.
;
;         b) Reads the data back into a RAM buffer
;
;************************************************************************
include "m8c.inc"        ; part specific constants and macros
include "memory.inc"     ; Constants and macros for SMM/LMM and Compiler
include "PSoCAPI.inc"    ; PSoC API definitions for all User Modules

ADDRESS_OFFSET:             equ      0
NUMBER_OF_BYTES:            equ      10
TEMPERATURE:                equ      25

export _main

export  abSerialNumberString
export  abInitialSerialNumber
export  abSerialNumberBuffer
export  bCounter
export  pPtr

    AREA    bss     (RAM,REL)

abInitialSerialNumber:    blk     NUMBER_OF_BYTES   ; string holds initial serial data
abSerialNumberBuffer:     blk     NUMBER_OF_BYTES   ; buffer to read back serial data
bCounter:                 blk     1                 ; counter to load initial string
pPtr:                     blk     1                 ; pointer to initial string

    AREA    text (ROM,REL)

;Table to hold initial serial number string
```

```
.LITERAL
abSerialNumberString:    db      '0','1','2','3','4','5','6','7','8','9'
.ENDLITERAL


_main:

; load the serialnumber into RAM
    mov    [bCounter], NUMBER_OF_BYTES        ; load 10 bytes from ROM into RAM


RAM_SETPAGE_MVR >abInitialSerialNumber
RAM_SETPAGE_MVW >abInitialSerialNumber
    mov    [pPtr], <abInitialSerialNumber ; ptr RAM data to put Flash data
    mov    X, <abSerialNumberString        ; LSB of abSerialNumberString
    mov    A, >abSerialNumberString          ; MSB of abSerialNumberString

; Use ROMX and MVI to copy the data from Flash to RAM
.loop:
    push   A                               ; Save MSB of abSerialNumberString to Stack
    romx
    mvi    [pPtr], A                        ; Save the value to RAM
    pop    A                               ; Get MSB of abSerialNumberString from Stack
    inc    X                               ; Increment LSB of abSerialNumberString
dec    [bCounter]
jnz    .loop


; Write the Serial Number - assume temp of 25C
    mov    A, TEMPERATURE                    ; temperature = 25C
    push   A
    mov    A, >NUMBER_OF_BYTES            ; MSB of wByteCount = 0
    push   A
    mov    A, <NUMBER_OF_BYTES          ; LSB of wByteCount = 10
    push   A
    mov    A, >abInitialSerialNumber      ; MSB of pbDest= >abInitialSerialNumber
    push   A
    mov    A, <abInitialSerialNumber   ; LSB of pbDest=abInitialSerialNumber
    push   A
    mov    A, >ADDRESS_OFFSET             ; MSB of wAddr=0
    push   A
    mov    A, <ADDRESS_OFFSET          ; LSB of wAddr=0
    push   A
    call   E2PROMx128_bE2Write                ; Write the data
    add    SP, -E2_WR_ARG_STACK_FRAME_SIZE
    pop    X


;if ( bError == NOERROR )
    cmp    A, 0
    jnz    .ExampleDone


; Read the Serial Number back into a RAM buffer
    mov    A, >NUMBER_OF_BYTES             ; MSB of wByteCount = 0
    push   A
    mov    A, <NUMBER_OF_BYTES          ; LSB of wByteCount = 10
```

```
        push    A
        mov     A, >abSerialNumberBuffer          ;MSB of pbDest= >abSerialNumberBuffer
        push    A
        mov     A, <abSerialNumberBuffer     ; LSB of pbDest=abInitialSerialNumber
        push    A
        mov     A, >ADDRESS_OFFSET               ; MSB of wAddr=0
        push    A
        mov     A, <ADDRESS_OFFSET          ; LSB of wAddr=0
        push    A
        call    E2PROMx128_E2Read
        add     SP, -E2_RD_ARG_STACK_FRAME_SIZE
        pop     X

.ExampleDone:
    jmp .ExampleDone
```

Version History

Version	Originator	Description
1.1	DHA	Added Version History
1.1.b	DHA	Updated assembler sample firmware source code.
1.1.c	DHA	Corrected ROM usage in user module datasheet.

Note   PSoC Designer 5.1 introduces a Version History in all user module datasheets. This section documents high level descriptions of the differences between the current and previous user module versions.